NSN 5961-01-302-3616

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Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-302-3616 **Inclosure Material:** Ceramic **Overall Length:** 0.785 inches **Terminal Length:** Between 0.125 inches and 0.200 inches **Overall Height:** 0.200 inches **Overall Width:** 0.320 inches **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor **Voltage Rating In Volts Per Characteristic:** 90.0 drain to source voltage all transistor and 90.0 drain to gate voltage all transistor and 40.0 gate to source voltage all transistor **Power Rating Per Characteristic:** 2.0 watts total device dissipation all transistor **Nuclear Hardness Critical Feature:** Hardened **Test Data Document:** 86360-743c4510-01 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing) **Terminal Type And Quantity:** 14 pin Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli